

CLAIMS

What is claimed is:

1. An integrated circuit structure, comprising:
NMOS and PMOS transistors, at least some of said PMOS transistors being formed in N-well diffusions in a semiconductor material; and
5 a blanket P-type diffusion component having a peak concentration depth more than twice that of said p-well.
2. An integrated circuit structure, comprising:
a first population of a first dopant in a semiconductor, said first population occupying a first region of said semiconductor;
a second population of said first dopant occupying a second region of
5 said semiconductor, said second region being at a deeper implant depth than said first region;
a second dopant occupying said second region of said semiconductor;
wherein said second dopant is of opposite electrical ionization than said first dopant.

3. A fabrication method, comprising the steps of:
- a) implanting first dopant atoms into a semiconductor body to create a first-conductivity-type well diffusion therein; and
 - b) implanting second dopant atoms into said semiconductor body,
5 with more than twice the stopping distance and less than one-quarter of the dosage per unit area as said step a), to compensate atoms which channeled during said step a).